

# isc N-Channel MOSFET Transistor IPD80R2K8CE,IIPD80R2K8CE

#### • FEATURES

- Static drain-source on-resistance:  $R_{DS}(on) \leq 2.8\Omega$
- Enhancement mode:
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRITION

• High peak current capability

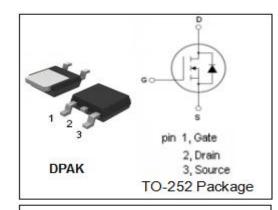


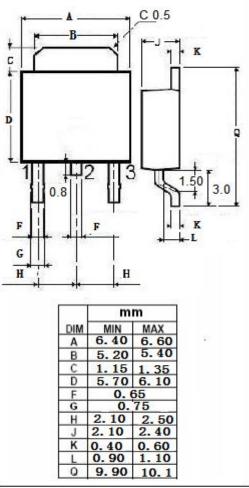
## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
$V_{ extsf{DSS}}$	Drain-Source Voltage	800	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
l <sub>D</sub>	Drain Current-Continuous	1.9	А
I <sub>DM</sub>	Drain Current-Single Pulsed	6	
$P_D$	Total Dissipation @T <sub>C</sub> =25℃	42	W
Tj	Max. Operating Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature	-55~150	$^{\circ}$

## • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(j-c)	Channel-to-case thermal resistance	3	°C/W
Rth(j-a)	Channel-to-ambient thermal resistance	62	°C/W







## isc N-Channel MOSFET Transistor

# IPD80R2K8CE,IIPD80R2K8CE

#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =0.25mA	800			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =0.12mA	2.1		3.9	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =1.1A			2.8	Ω
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = 20V;V <sub>DS</sub> =0V			0.1	μ <b>A</b>
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =800V; V <sub>GS</sub> = 0V			5	μА
$V_{SD}$	Diode forward voltage	I <sub>F</sub> =1.9A, V <sub>GS</sub> = 0V			1.2	V

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